

REMARKS

Claim Rejection 35 U.S.C. § 112

The Examiner has rejected claim 22 under 35 U.S.C § 112, second paragraph, as being indefinite for failing to particularly point out and distinctly claim the subject matter which applicant regards as the invention. Applicant has amended claim 22 to more particularly point out and distinctly claim the subject matter which Applicant regards as the invention. As such, Applicant respectfully requests the Examiner to remove the 35 U.S.C § 112 rejection of claim 22.

Claim Rejections - 35 U.S.C. § 102/103

The Examiner has rejected claims 1-4, 6-8, 11-16, 20 to 25 and 29-31 under 35 U.S.C. 102(b) as being anticipated by Wu, et al., (US Patent 6,309,975). Additionally, the Examiner has rejected claims 5, 9, 10 under 35 U.S.C. 103(a) as being unpatentable over Wu, et al., (US Patent No. 6,309,975) and Nihonmatsu, et al., (US Patent No. 6,346,485).

In claims 1-16 and 20-22, Applicant teaches and claims a method of patterning a crystalline film. Applicant claims to place dopant atoms into a first region of the crystalline film whereby the dopant atoms make the portion of the crystalline film in the first region nondegenerate or less degenerate than the crystalline film which was not doped (second region). An etchant is then used to etch away the second region without etching the first region. Thus, Applicant claims that the region which is doped (first region) remains while the region which was undoped (second region) is removed.

Wu, et al., describes a process wherein an undoped intrinsic silicon film 14 is formed on a silicon substrate 12. A photoresist mask 16 is then formed on a portion of the polysilicon film 14. (Figure 1) Ions 20 are then implanted into the polysilicon film 14 on either side of mask 16 to form doped regions of polysilicon layer 14. Next, the photoresist mask 16 is removed. The substrate then is exposed to and etched which removes the doped regions of polysilicon layer 14, but does not remove the undoped region 30 of polysilicon layer 14. Thus, in Wu the regions that have been implanted are etched away while the regions which have not been implanted remain. Accordingly, in Wu areas which have been implanted (first regions) are etched away, while regions that were not implanted (second region) remain as opposed to Applicant's claim invention wherein the regions which has been doped (first region) remains while the regions which are not doped (second region) are removed.

As such, for the above mentioned reasons, it is Applicant's understanding that the cited references fail to teach or rendered obvious Applicant's invention as claimed in claims 1-16 and 20-22. Applicant, therefore respectfully requests the removal of 35 U.S.C § 102 and 103 rejections of claims 1-16 and 20-22 and seeks and early allowance of these claims.